# 2SD2598

### Silicon NPN epitaxial planar type darlington

#### For low-frequency amplification

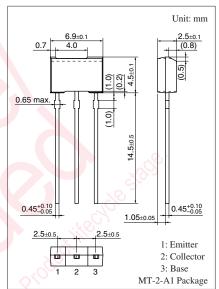
#### ■ Features

- Forward current transfer ratio h<sub>FE</sub> is designed high, which is appropriate to the driver circuit of motors and printer hammer
- A shunt resistor is omitted from the driver.
- M type package, allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

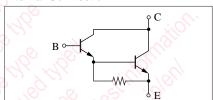
#### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	$V_{CBO}$	60	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V	
Collector current	$I_{C}$	500	mA	
Peak collector current	$I_{CP}$	750	mA	
Collector power dissipation *	P <sub>C</sub>	1	W	
Junction temperature	T <sub>j</sub>	150	°CO	
Storage temperature	$T_{stg}$	-55 to +150	°C	

Note) \*: Printed circuit board: Copper foil area of 1 cm<sup>2</sup> or more, and the board thickness of 1.7 mm for the collector portion



#### Internal Connection



### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_C = 100  \mu A, I_E = 0$	60			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 1 \text{ mA}, I_B = 0$	50			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_E = 100  \mu A, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 25 \text{ V}, I_{E} = 0$			100	nA
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 4 \text{ V}, I_{C} = 0$			100	nA
Forward current transfer ratio *1, 2	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_{C} = 500 \text{ mA}$	4000		20 000	_
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_C = 500 \text{ mA}, I_B = 0.5 \text{ mA}$			2.5	V
Base-emitter saturation voltage *1	V <sub>BE(sat)</sub>	$I_C = 500 \text{ mA}, I_B = 0.5 \text{ mA}$			3.0	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz

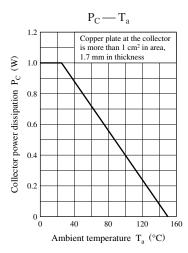
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

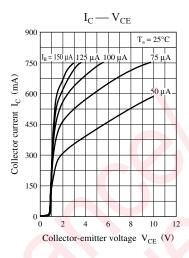
2. \*1: Pulse measurement

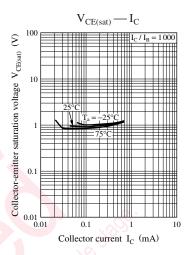
\*2: Rank classification

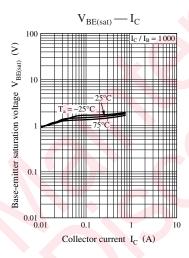
Rank	Q	R
h <sub>FE</sub>	4000 to 10000	8 000 to 20 000

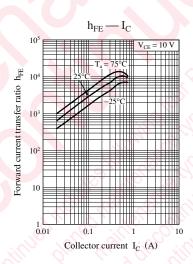
## **Panasonic**

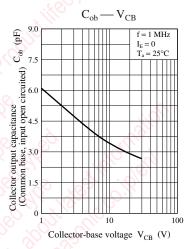












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